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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# MOS FIELD EFFECT TRANSISTOR $\mu PA650TT$

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### **DESCRIPTION**

The  $\mu PA650TT$  is a switching device, which can be driven directly by a 1.8 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

#### **FEATURES**

- 1.8 V drive available
- · Low on-state resistance

RDS(on)1 = 50 m $\Omega$  MAX. (VGS = -4.5 V, ID = -2.5 A)

RDS(on)2 = 68 m $\Omega$  MAX. (Vgs = -2.5 V, ID = -2.5 A)

RDS(on)3 = 114 m $\Omega$  MAX. (VGS = -1.8 V, ID = -1.5 A)

#### ORDERING INFORMATION

PART NUMBER	PACKAGE				
μPA650TT	6pinWSOF (1620)				

Marking: WD

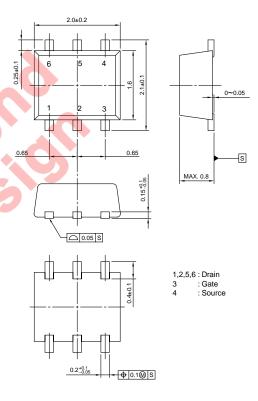
#### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-12	V
Gate to Source Voltage (VDS = 0 V)	Vgss	∓8.0	V
Drain Current (DC) (T <sub>A</sub> = 25°C)	ID(DC)	∓5.0	Α
Drain Current (pulse) Note1	ID(pulse)	∓20	Α
Total Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>T1</sub>	0.2	W
Total Power Dissipation (T <sub>A</sub> = 25°C) Note	P <sub>T2</sub>	1.4	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

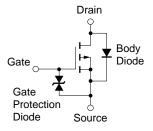
**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

**2.** Mounted on FR-4 board,  $t \le 5$  sec.

#### PACKAGE DRAWING (Unit: mm)



#### **EQUIVALENT CIRCUIT**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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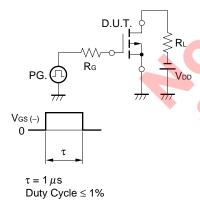
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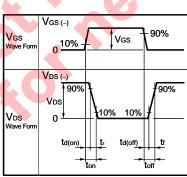


**ELECTRICAL CHARACTERISTICS (TA = 25°C)** 

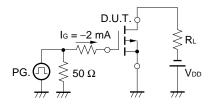
	1					
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = −12 V, V <sub>GS</sub> = 0 V			-10	μΑ
Gate Leakage Current	Igss	$V_{GS} = \mp 8.0 \text{ V}, V_{DS} = 0 \text{ V}$			∓10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1.0 \text{ mA}$	-0.45		-1.5	V
Forward Transfer Admittance	<b>y</b> fs	$V_{DS} = -10 \text{ V}, I_{D} = -2.5 \text{ A}$	4.0			S
Drain to Source On-state Resistance	RDS(on)1	Vgs = -4.5 V, ID = -2.5 A		40	50	mΩ
	RDS(on)2	Vgs = -2.5 V, ID = -2.5 A		51	68	mΩ
	RDS(on)3	V <sub>GS</sub> = −1.8 V, I <sub>D</sub> = −1.5 A		68	114	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = −10 V		610		pF
Output Capacitance	Coss	Vgs = 0 V		150		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		100		pF
Turn-on Delay Time	td(on)	$V_{DD} = -6.0 \text{ V}, \text{ ID} = -2.5 \text{ A}$		50		ns
Rise Time	<b>t</b> r	Vgs = −4.0 V		200		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		400		ns
Fall Time	t <sub>f</sub>			315		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = −10 V		5.5		nC
Gate to Source Charge	Q <sub>GS</sub>	Vgs = -4.0 V		1.5		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = -5.0 A		1.6		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	I <sub>F</sub> = 5.0 A, V <sub>GS</sub> = 0 V		0.89		٧

#### **TEST CIRCUIT 1 SWITCHING TIME**



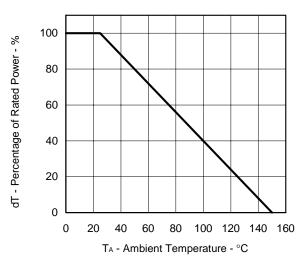


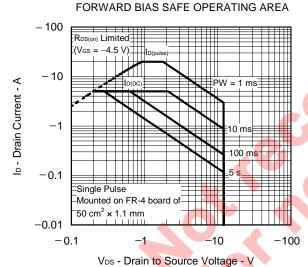
#### **TEST CIRCUIT 2 GATE CHARGE**



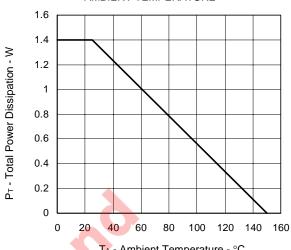
#### TYPICAL CHARACTERISTICS (TA = 25°C)

#### DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



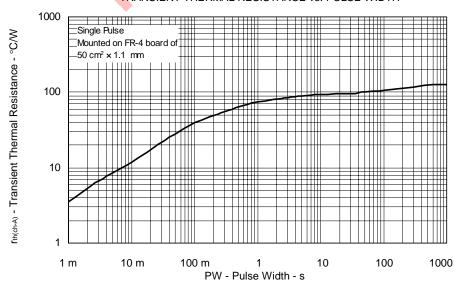


#### TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



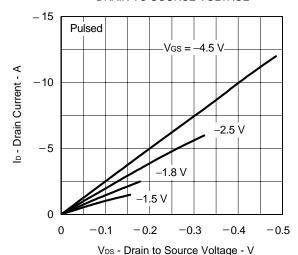
#### TA - Ambient Temperature - °C

#### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

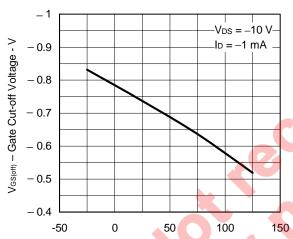


3

#### DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

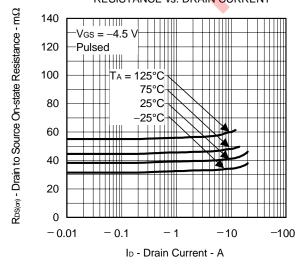


## GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

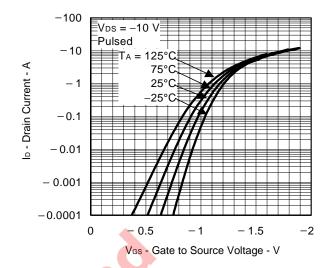


DRAIN TO SOURCE ON-STATE
RESISTANCE vs. DRAIN CURRENT

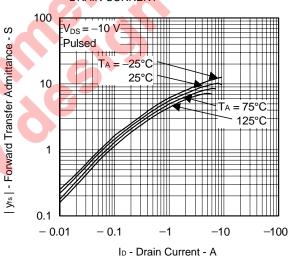
Tch - Channel Temperature - °C



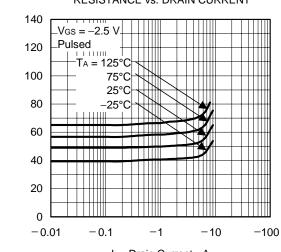
#### FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



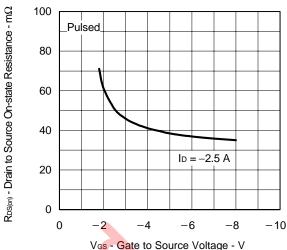
ID - Drain Current - A

RDS(on) - Drain to Source On-state Resistance - m\Omega

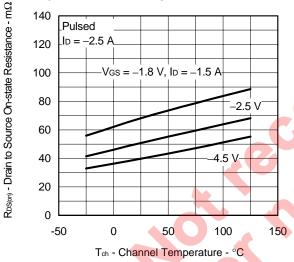
#### RESISTANCE vs. DRAIN CURRENT 140 $\mathsf{Res}_{(m)}$ - Drain to Source On-state Resistance - $m\Omega$ $V_{GS} = -1.8 \text{ V}$ -Pulsed 120 100 80 60 $T_A = 125$ °C 40 75°C 25°C 20 -25°C|{ 0 -0.01-0.1-10-100 ID - Drain Current - A

DRAIN TO SOURCE ON-STATE

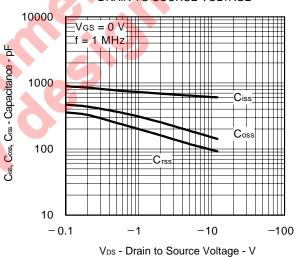




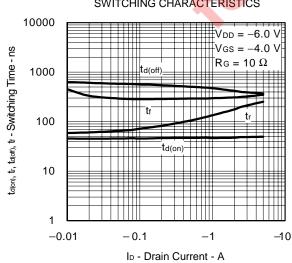




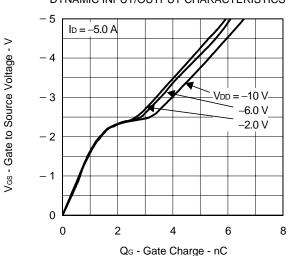
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

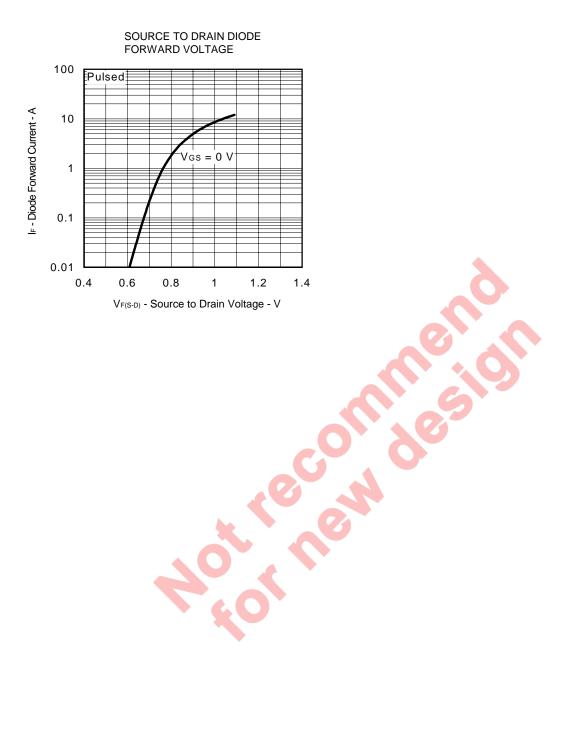


#### SWITCHING CHARACTERISTICS



#### DYNAMIC INPUT/OUTPUT CHARACTERISTICS





[MEMO]



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